



1. Title:	Improved EUV Photoresist Performance through Processing Refinements
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3. Abstract body:

In this presentation, we discuss results obtained from EUV exposures using the 0.3 NA MET at Lawrence Berkeley National Laboratories, USA. We present a series of results exploring process-related improvements to EUV resist performance. These include optimization of process temperatures, development refinements including use of surface-conditioning reagents, and substrate treatments. Process refinements are capable of significantly expanding exposure latitude, mitigating resist failure mechanisms, and attenuating line-edge and line-width roughness. We examine these improvements in the context of future technology node requirements for which EUV technology is a candidate, investigate appropriate metrics for quantitating resist performance improvements, and present mechanistic interpretations for observed process improvement.